

GT100HH120T2H IGBT Module

Preliminary Data

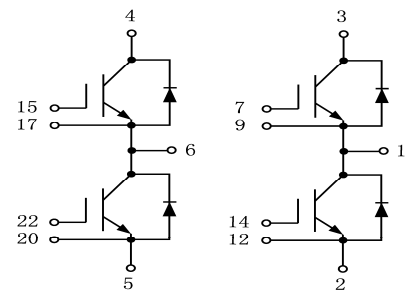
Features:

- Short Circuit Rated 10 μ s
- Low Saturation Voltage: $V_{CE} (sat) = 1.90V @ I_C = 100A, T_C = 25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested ($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Industrial Inverters
- Servo Applications
- EV And EHV
- Induction Heating



IGBT, Inverter

Maximum Rated Values ($T_C = 25^\circ C$ Unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C,$	100	A
		$T_C = 25^\circ C$	200	A
I_{CM}	Peak Collector Current Repetitive	$T_J = 175^\circ C$	200	A
t_{SC}	Short Circuit Withstand Time		>10	μ s
P_D	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C$ $T_{Jmax} = 175^\circ C$	575	W



Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ Unless otherwise specified)

Static characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	5.0	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\text{A}, V_{GE} = 15\text{V}$	$T_J = 25^\circ\text{C}$	1.90	2.10	V
			$T_J = 125^\circ\text{C}$	2.20		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^\circ\text{C}$			200	nA
C_{ies}	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		13.7		nF
C_{oes}	Output capacitance			0.78		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 100\text{A}, R_G = 15\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J = 25^\circ\text{C}$	240	ns
			$T_J = 125^\circ\text{C}$	225	
t_r	Rise Time		$T_J = 25^\circ\text{C}$	140	ns
			$T_J = 125^\circ\text{C}$	145	
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$	420	ns
			$T_J = 125^\circ\text{C}$	450	
t_f	Fall Time		$T_J = 25^\circ\text{C}$	170	ns
			$T_J = 125^\circ\text{C}$	230	
E_{on}	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$	9.1	mJ
			$T_J = 125^\circ\text{C}$	11.7	
E_{off}	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$	5.5	mJ	
		$T_J = 125^\circ\text{C}$	7.9		
Q_g	Total Gate Charge	$T_J = 25^\circ\text{C}$	950	nC	
RBSOA	RBSOA	$I_C=200\text{A}, V_{CC}=1050\text{V}, V_p=1200\text{V}, R_g = 15\Omega, V_{GE}=\pm 15\text{V to } 0\text{V}, T_J = 150^\circ\text{C}$	Trapezoid		
SCSOA	SCSOA	$V_{CC} = 600\text{V}, V_{GE} = 15\text{V}, T_J = 150^\circ\text{C}$	10		μs
$R_{\theta JC}$	Junction-To-Case (Per Leg)		0.26		$^\circ\text{C/W}$



Diode, Inverter

Maximum Rated Values ($T_C=25^{\circ}\text{C}$ Unless otherwise specified)

V_{RRM}	Repetitive peak reverse voltage	1200	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Peak FWD Current Repetitive	200	A

Electrical Characteristics of FWD ($T_C=25^{\circ}\text{C}$ Unless otherwise specified)

V_{FM}	Forward Voltage	$I_F = 100\text{A}$, $V_{GE} = 15\text{V}$	$T_J = 25^{\circ}\text{C}$	2.2	V
			$T_J = 125^{\circ}\text{C}$	2.5	
I_{rr}	Peak Reverse Recovery Current	$I_F = 100\text{A}$, $di/dt = 650\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	40	A
			$T_J = 125^{\circ}\text{C}$	50	
Q_{rr}	Reverse Recovery Charge	$I_F = 100\text{A}$, $di/dt = 650\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	4.7	μC
			$T_J = 125^{\circ}\text{C}$	10.6	
E_{rec}	Reverse Recovery Energy	$I_F = 100\text{A}$, $di/dt = 650\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	2.3	mJ
			$T_J = 125^{\circ}\text{C}$	4.1	
$R_{\theta JC}$	Junction-To-Case (Per Leg)			0.54	$^{\circ}\text{C}/\text{W}$

Module

Symbol	Description	Min	Typ	Max	Unit
V_{iso}	Isolation Voltage(All Terminals Shorted)	$f = 50\text{Hz}$, 1minute	2500		V
T_J	Maximum Junction Temperature			175	$^{\circ}\text{C}$
T_{JOP}	Maximum Operating Junction Temperature Range	-40		+150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-40		+125	$^{\circ}\text{C}$
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)		0.1		$^{\circ}\text{C}/\text{W}$
M	Power Terminals Screw:M5	3.0		5.0	N·m
M	Mounting Screw:M6	4.0		6.0	N·m
G	Weight		280		g

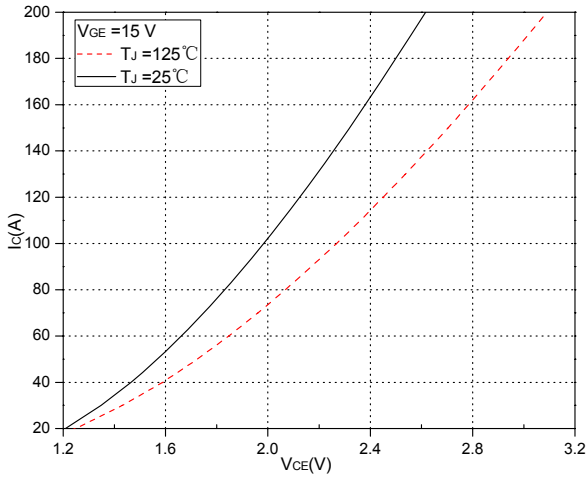


Fig.1 Typical Saturation Voltage Characteristics

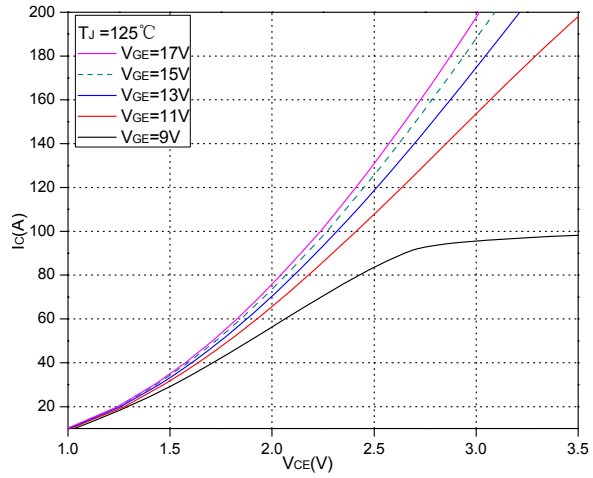


Fig.2 Typical Output Characteristics

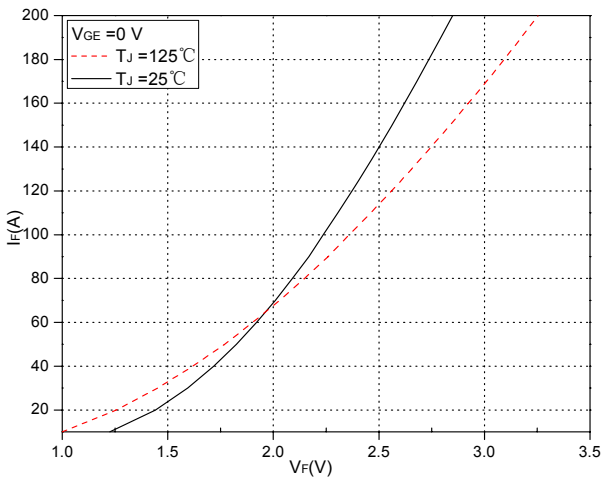


Fig.3 Forward Characteristics of FWD

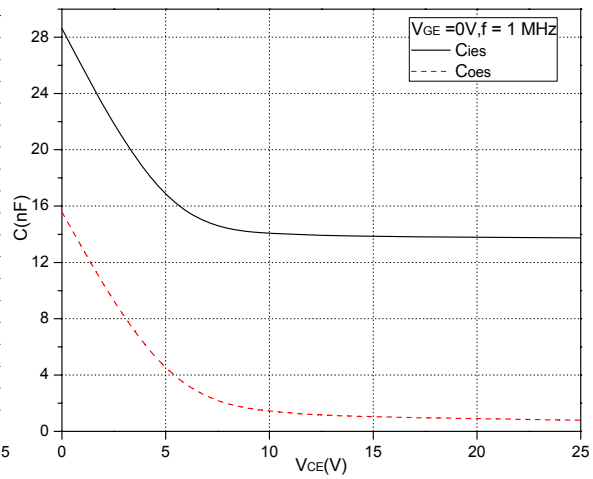


Fig.4 Capacitance Characteristics

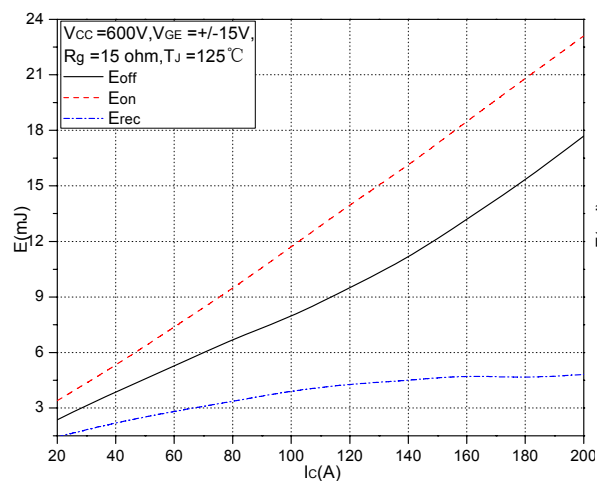


Fig.5 Typical Switching Loss vs. Collector Current

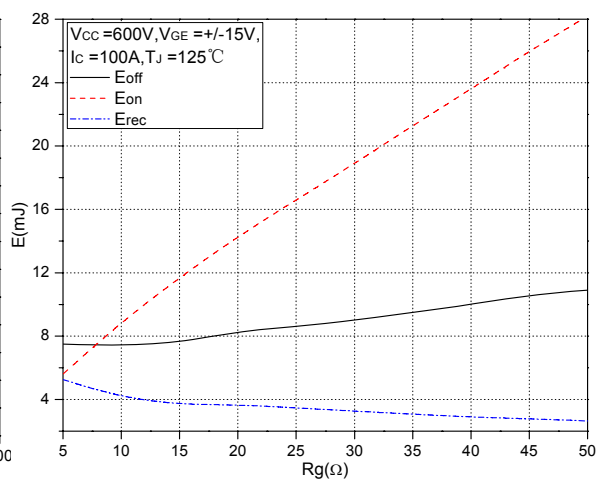


Fig.6 Typical Switching Loss vs. Gate Resistance

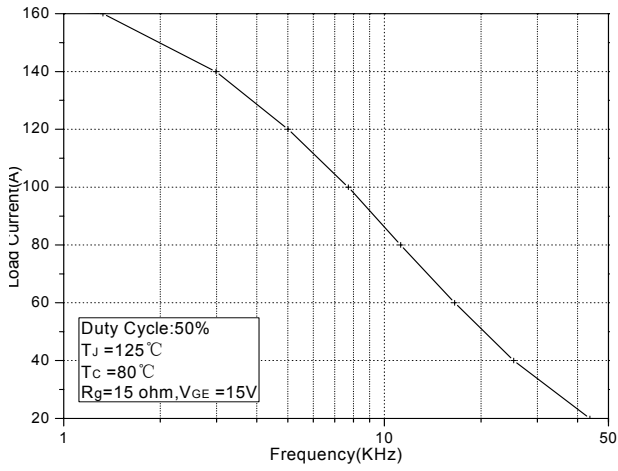


Fig.7 Typical Load Current vs. Frequency

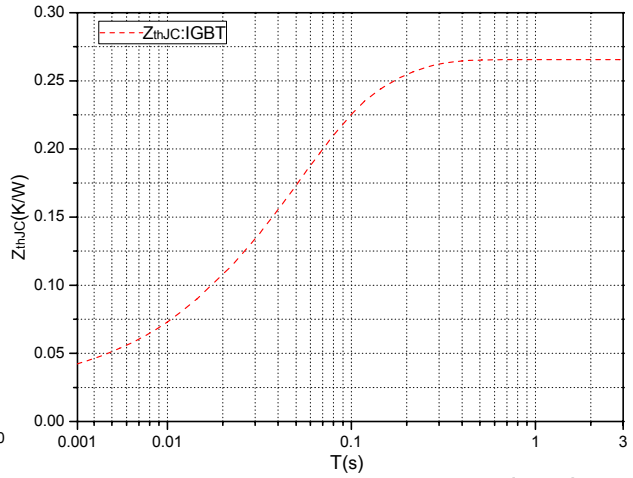


Fig.8 Transient thermal impedance (IGBT)

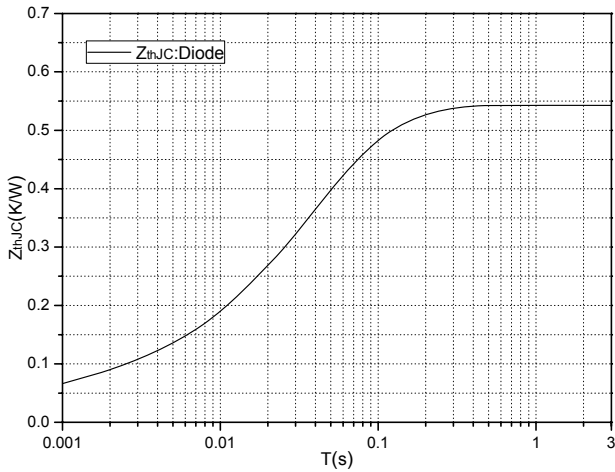


Fig.9 Transient thermal impedance (Diode)

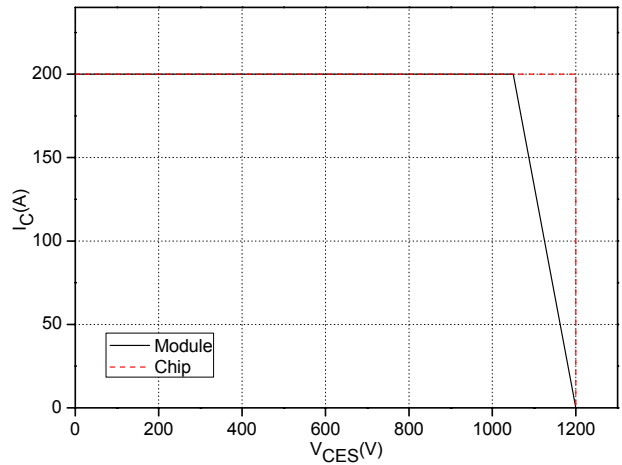
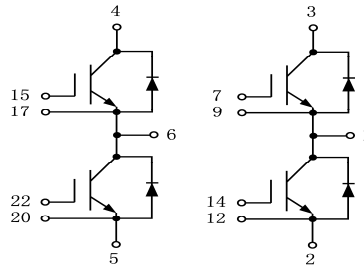
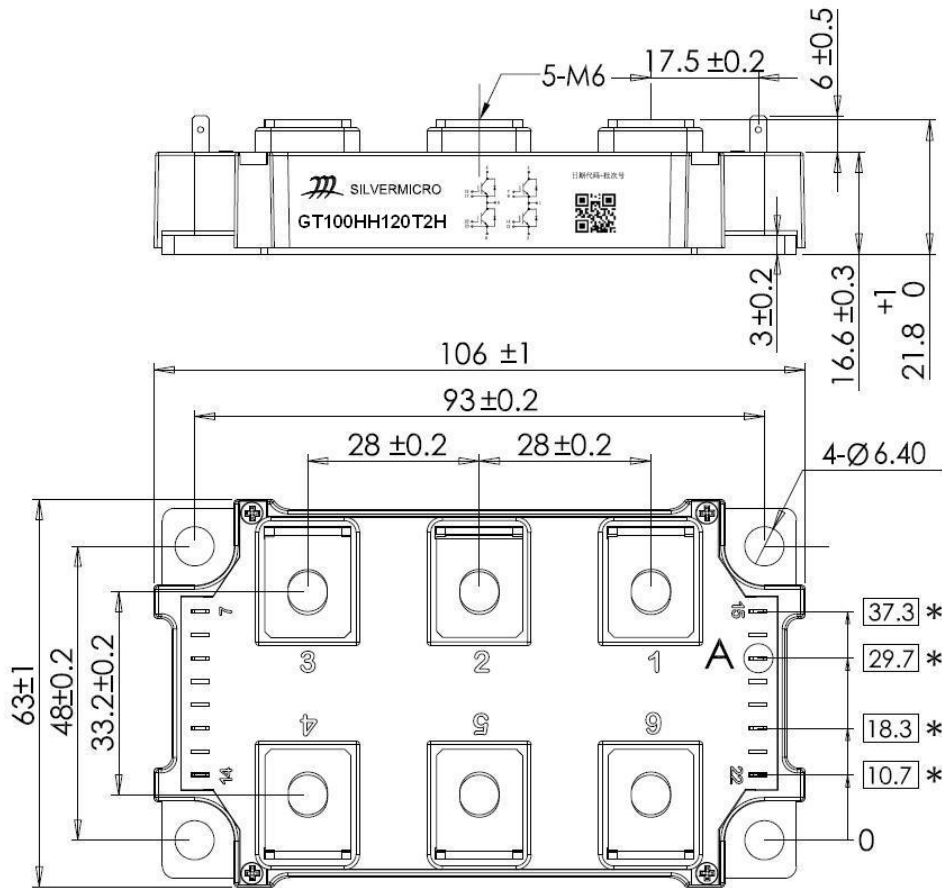


Fig.10 Reverse Bias Safe Operation Area (RBSOA)

Internal Circuit:



Package Outline (Unit: mm):



* =all dimensions with tolerance of ± 0.5

**Announcement**

Information in this document is believed to be accurate and reliable. However, NJSME does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes

NJSME reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.